

MiniSKiiP® 3

3-phase bridge rectifier +  
brake chopper

SKiiP 39AHB16V1

## Features

- Fast Trench IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

## Typical Applications\*

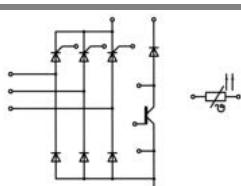
- Input bridge for inverter up to 45 kVA

## Remarks

- $V_{CEsat}$ ,  $V_F$  = chip level value

Absolute Maximum Ratings		$T_s = 25^\circ\text{C}$ , unless otherwise specified		
Symbol	Conditions	Values		Units
<b>IGBT - Chopper</b>				
$V_{CES}$		1200		V
$I_C$	$T_s = 25 (70)^\circ\text{C}$	157 (118)		A
$I_{CRM}$	$t_p \leq 1 \text{ ms}$	280		A
$V_{GES}$		$\pm 20$		V
$T_j$		- 40 ... + 150		$^\circ\text{C}$
<b>Diode - Chopper</b>				
$I_F$	$T_s = 25 (70)^\circ\text{C}$	167 (124)		A
$I_{FRM}$	$t_p \leq 1 \text{ ms}$	280		A
$T_j$		- 40 ... + 150		$^\circ\text{C}$
<b>Diode / Thyristor - Rectifier</b>				
$V_{RRM}$		1600		V
$I_F / I_T$	$T_s = 70^\circ\text{C}$	121		A
$I_{FSM} / I_{TSM}$	$t_p = 10 \text{ ms, sin } 180^\circ, T_j = 25^\circ\text{C}$	1250		A
$i_{\text{t}}$	$t_p = 10 \text{ ms, sin } 180^\circ, T_j = 25^\circ\text{C}$	7800		A <sup>2</sup> s
$T_j$	Diode	- 40 ... + 150		$^\circ\text{C}$
$T_j$	Thyristor	- 40 ... + 125		$^\circ\text{C}$
$I_{tRMS}$	per power terminal (20 A / spring)	160		A
$T_{\text{stg}}$	$T_{\text{op}} \leq T_{\text{stg}}$	- 40 ... + 125		$^\circ\text{C}$
$V_{\text{isol}}$	AC, 1 min.	2500		V

Characteristics		$T_s = 25^\circ\text{C}$ , unless otherwise specified		
Symbol	Conditions	min.	typ.	max.
<b>IGBT - Chopper</b>				
$V_{CEsat}$	$I_{Cnom} = 140 \text{ A}, T_j = 25 (125)^\circ\text{C}$		1,7 (2)	2,1 (2,4)
$V_{GE(\text{th})}$	$V_{GE} = V_{CE}, I_C = 6 \text{ mA}$	5	5,8	6,5
$V_{CE(\text{TO})}$	$T_j = 25 (125)^\circ\text{C}$		1 (0,9)	1,2 (1,1)
$r_T$	$T_j = 25 (125)^\circ\text{C}$		5 (7,9)	6,4 (9,3)
$C_{ies}$	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$		11,2	nF
$C_{oes}$	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$		1,9	nF
$C_{res}$	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$		1,5	nF
$R_{th(j-s)}$	per IGBT		0,3	K/W
$t_{d(on)}$	under following conditions		80	ns
$t_r$	$V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}$		40	ns
$t_{d(off)}$	$I_{Cnom} = 140 \text{ A}, T_j = 125^\circ\text{C}$		500	ns
$t_f$	$R_{Gon} = R_{Goff} = 5 \Omega$		100	ns
$E_{on}$	inductive load		19,9	mJ
$E_{off}$			17,3	mJ
<b>Diode - Chopper</b>				
$V_F = V_{EC}$	$I_{Fnom} = 140 \text{ A}, T_j = 25 (125)^\circ\text{C}$		1,5 (1,5)	1,7 (1,7)
$V_{(TO)}$	$T_j = 25 (125)^\circ\text{C}$		1 (0,8)	1,1 (0,9)
$r_T$	$T_j = 25 (125)^\circ\text{C}$		3,6 (5)	4,3 (5,7)
$R_{th(j-s)}$	per diode		0,4	K/W
$I_{RRM}$	under following conditions		210	A
$Q_{rr}$	$I_{Fnom} = 140 \text{ A}, V_R = 600 \text{ V}$		38	$\mu\text{C}$
$E_{rr}$	$V_{GE} = 0 \text{ V}, T_j = 125^\circ\text{C}$ $di_F/dt = 4300 \text{ A}/\mu\text{s}$		16,2	mJ



AHB

Characteristics		$T_s = 25^\circ\text{C}$ , unless otherwise specified		
Symbol	Conditions	min.	typ.	max.
Diode - Rectifier				
$V_F$	$I_{F\text{nom}} = 90\text{ A}$ , $T_j = 25^\circ\text{C}$		1,2	V
$V_{(TO)}$	$T_j = 150^\circ\text{C}$		0,8	V
$r_T$	$T_j = 150^\circ\text{C}$		4	$\text{m}\Omega$
$R_{\text{th}(j-s)}$	per diode		0,5	K/W
Thyristor - Rectifier				
$V_T$	$I_{F\text{nom}} = 200\text{ A}$ , $T_j = 25\text{ (125)}^\circ\text{C}$		1,65 (1,6)	V
$V_{T\text{(TO)}}$	$T_j = 125^\circ\text{C}$		0,9	V
$r_T$	$T_j = 125^\circ\text{C}$		3,5	$\text{m}\Omega$
$V_{GT}$	$T_j = 25^\circ\text{C}$		3	V
$I_{GT}$	$T_j = 25^\circ\text{C}$	150		$\text{mA}$
$I_H$	$T_j = 25^\circ\text{C}$	150		$\text{mA}$
$I_L$	$T_j = 25^\circ\text{C}$	300		$\text{mA}$
$dv/dt_{(cr)}$	$T_j = 125^\circ\text{C}$		1000	$\text{V}/\mu\text{s}$
$di/dt_{(cr)}$	$T_j = 125^\circ\text{C}$		100	$\text{A}/\mu\text{s}$
$R_{\text{th}(j-s)}$	per thyristor		0,5	K/W
Temperature Sensor				
$R_{ts}$	$3\%$ , $T_r = 25\text{ (100)}^\circ\text{C}$		1000(1670)	$\Omega$
Mechanical Data				
w		95		g
$M_s$	Mounting torque	2	2,5	Nm

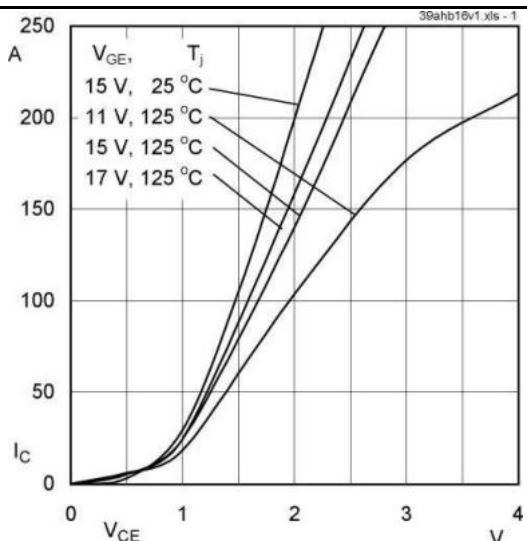


Fig. 1 Typ. output characteristic

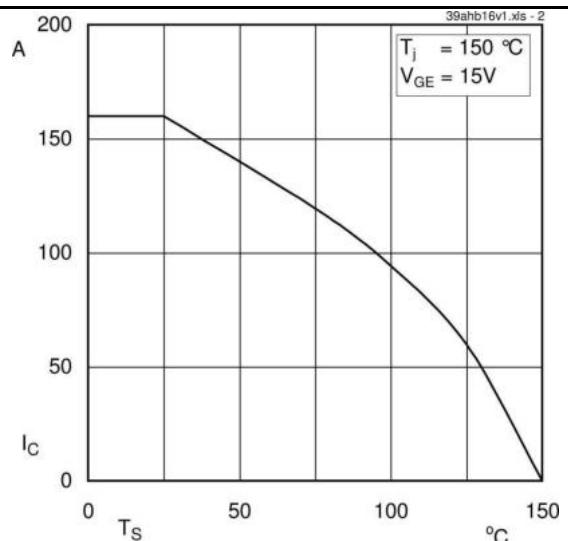


Fig. 2 Typ. rated current vs. temperature

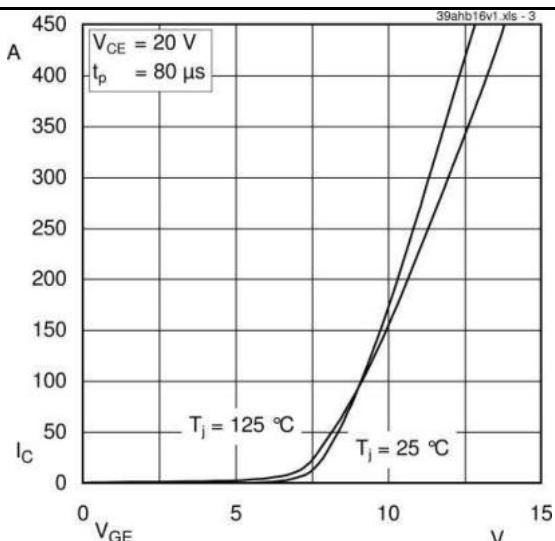


Fig. 3 Typ. transfer characteristic

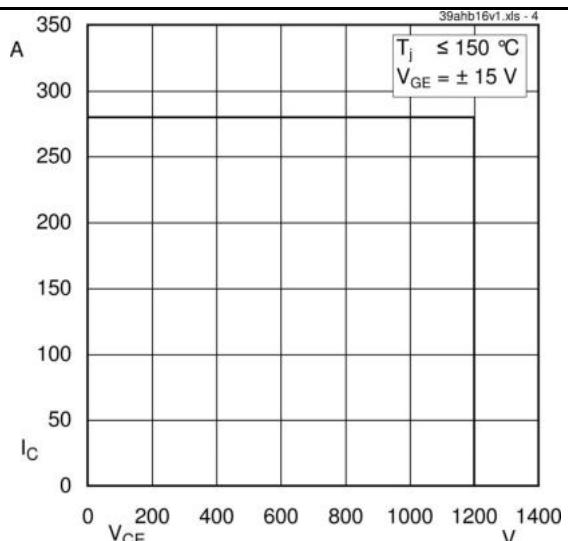


Fig. 4 Reverse bias safe operating area

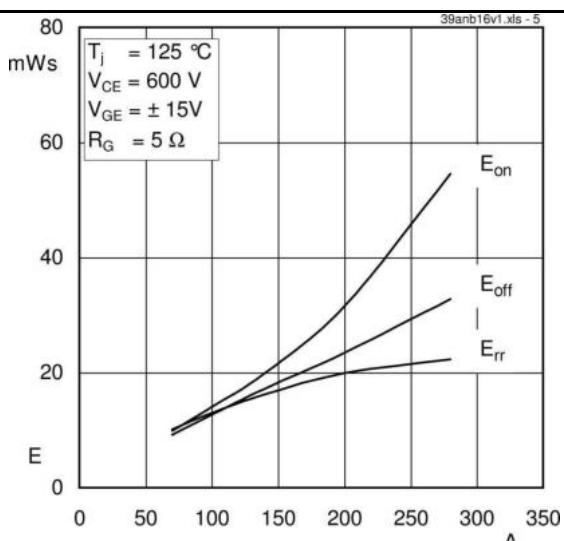


Fig. 5 Typ. Turn-on /-off energy = f ( $I_C$ )

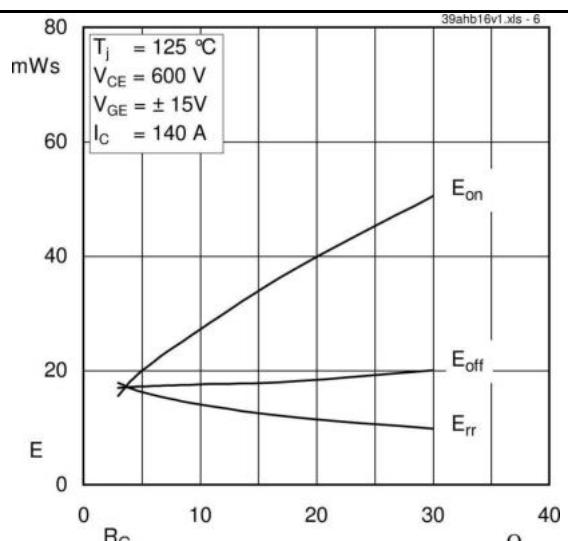
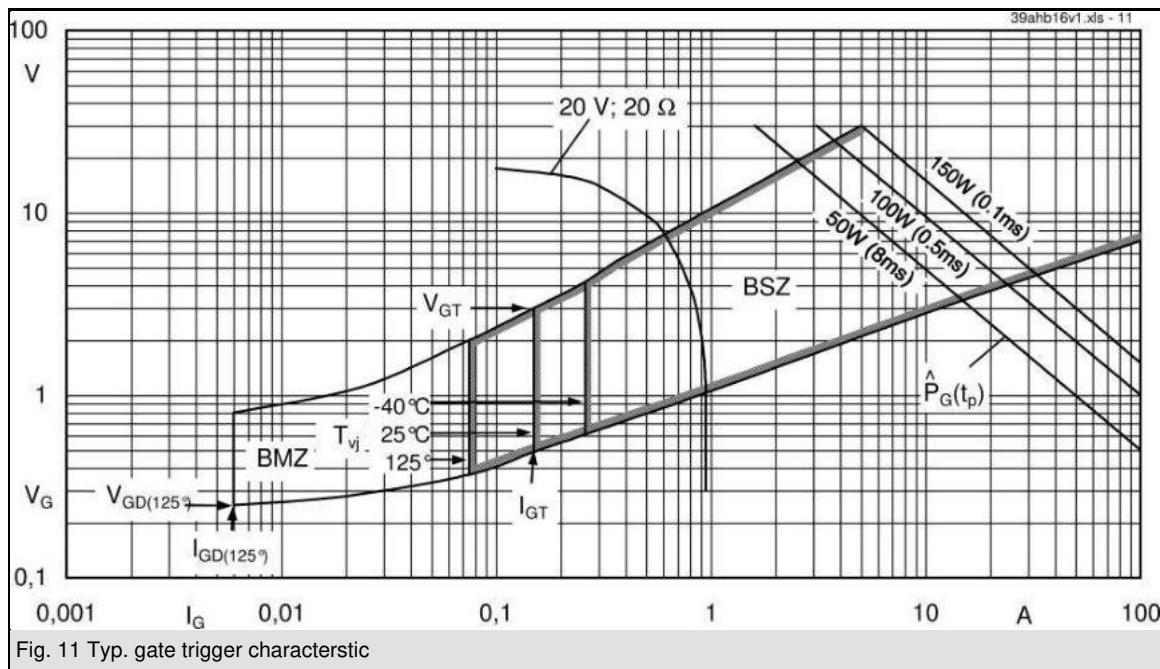
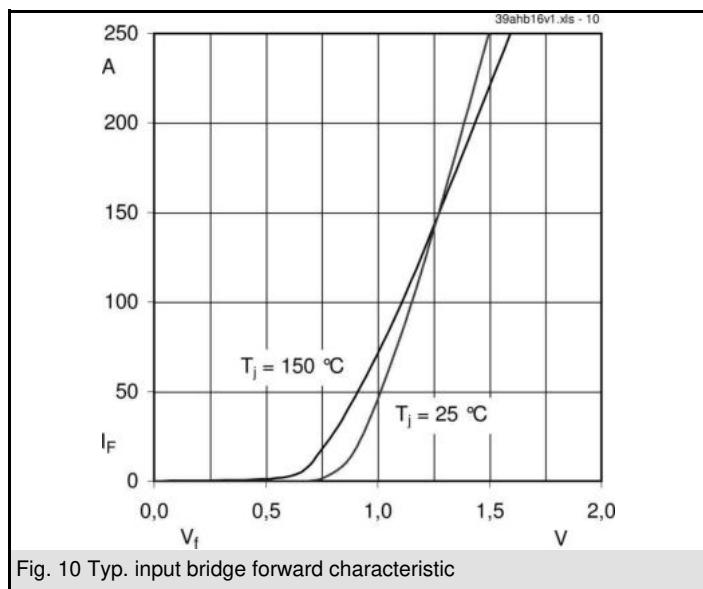
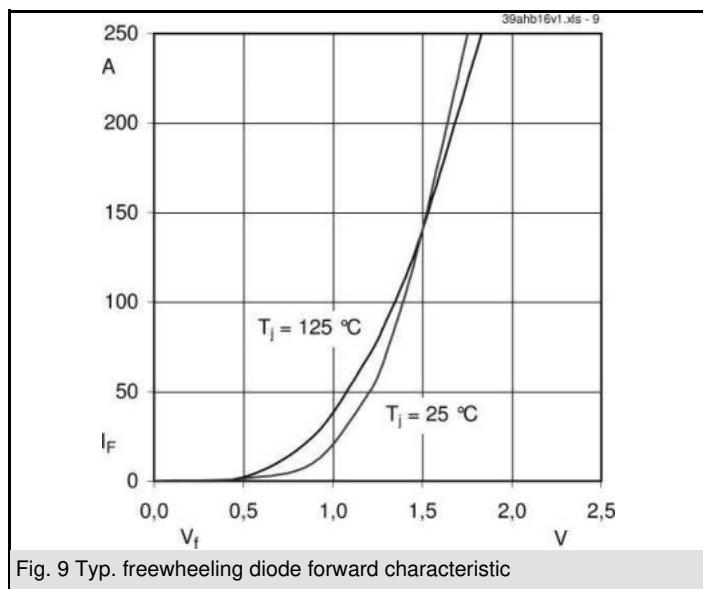
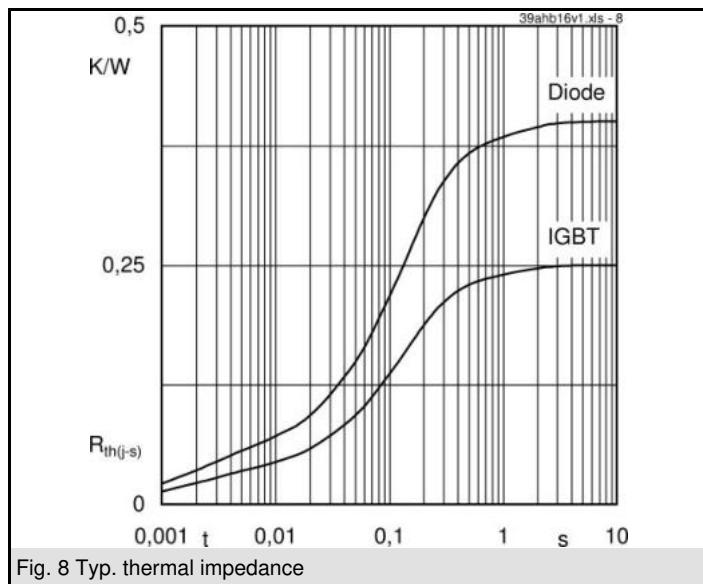
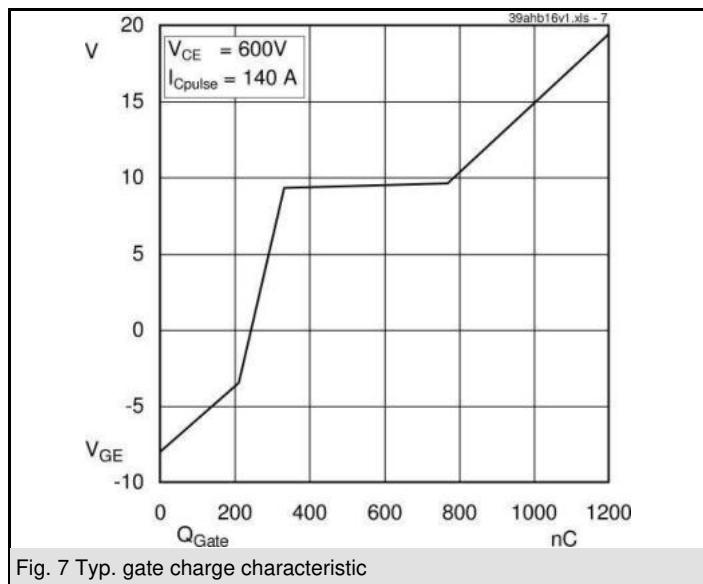
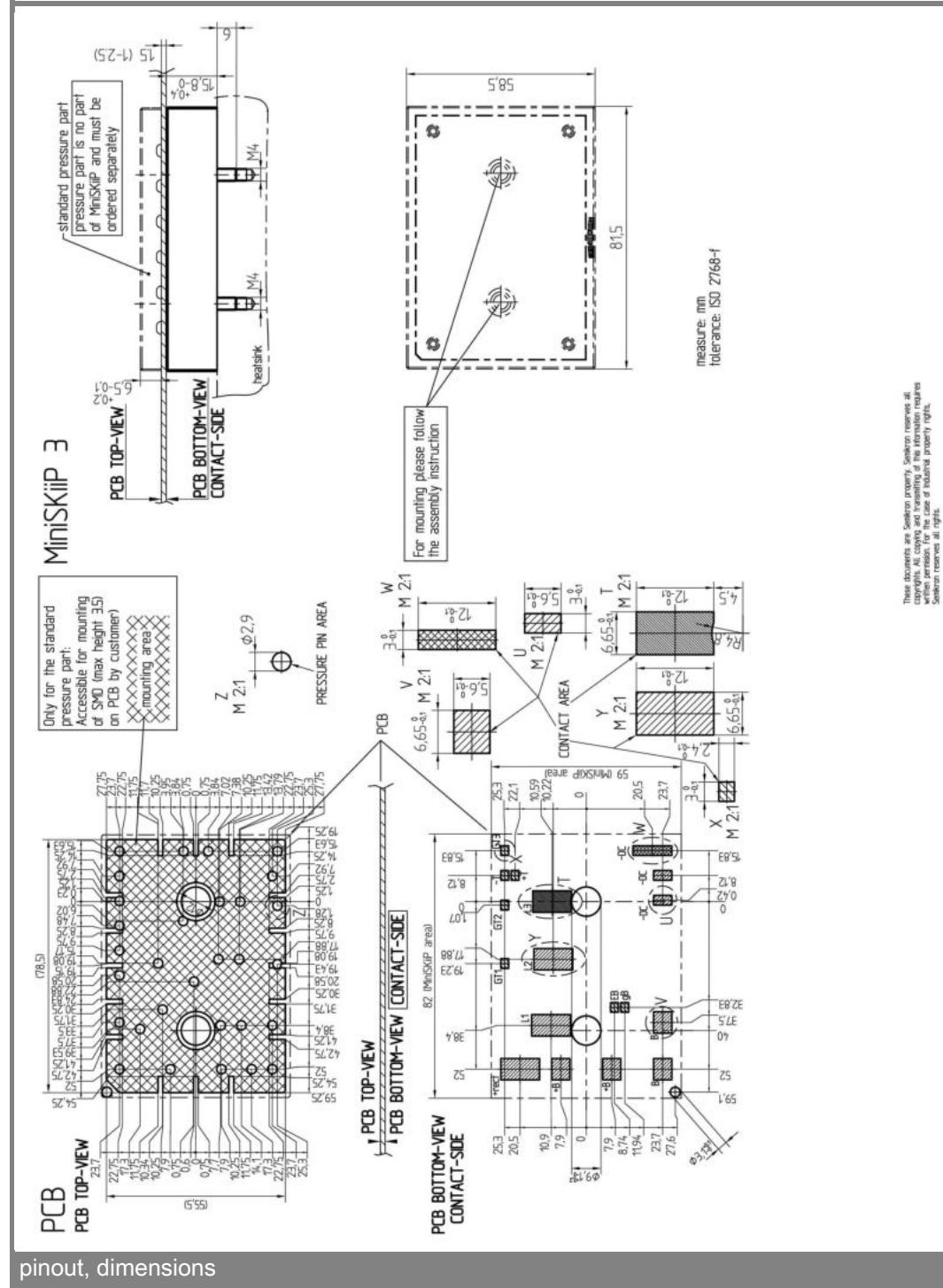
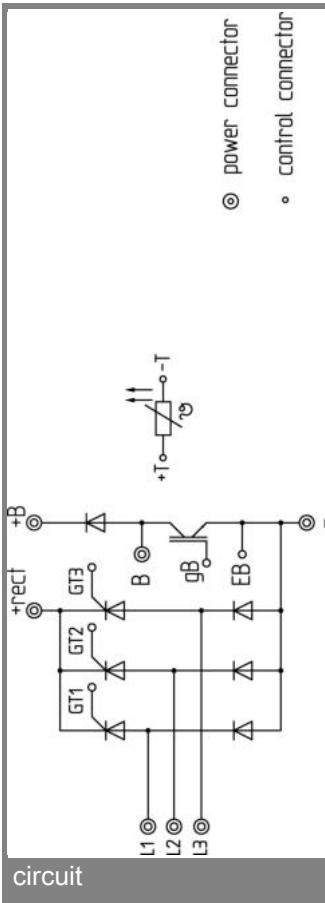


Fig. 6 Typ. Turn-on /-off energy = f ( $R_G$ )

# SKiiP 39AHB16V1





This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.